

Francesco La Via was born in Catania, Italy, in September 1961. He received the M.S. degree in physics from Catania University, Catania, Italy, in 1985. From 1985 to 1990, he had a fellowship at SGS-Thompson, Catania. In 1990, he joined the CNR Institute for Microelectronic, Catania as a researcher. During this time, he also spent nine months as a Visiting Scientist at Philips National Laboratory, Eindhoven, The Netherlands, working on a project for the use of epitaxial cobalt silicide in permeable base transistors.

In 2001 he became senior researcher of the CNR Institute for Microelectronic and Microsensors and he is responsible of the research group that work on the new metallization schemes for silicon and silicon carbide. From 2003 he is responsible of the division of CNR-IMM that developed new CVD reactors and new processes for silicon carbide epitaxy and hetero-epitaxy. From 2020 he is Research Director at CNR-IMM. He is responsible of several industrial research projects in the field of SiC epitaxial growth and new systems for CVD and sublimation growth. He is coordinator of two European Research Project on the growth of 3C-SiC on silicon and on the applications in the field of power devices (CHALLENGE) and of MEMS for geophysics (SiC nano for picoGeo).

In this period, he has published more than 350 papers on JCR journals and several review and book chapters. He has presented several invited contributions to international conferences and has organized several conference and tutorials. He is referee of several international journals: Applied Physics Letters, Journal of Applied Physics, Journal of Material Research, IEEE Transaction on Electron Devices, Journal of Electrochemical Society, Chemical Vapour Deposition, Materials, Micromachines,